

IN THE SPECIFICATION

Please amend the indicated portions of the specification as follows:

[0028] In the light sensor circuit, once the drain voltage V_D of the MOS type transistor Q1 was switched over to the low level L for initializing the circuit, the transistor Q1 is brought into the low-resistance state if a potential between the gate voltage V_G and the drain voltage V_D is greater than a threshold of the transistor Q1. Therefore, the source side potential at that moment becomes equal to the drain voltage V_D (a difference between potentials still remains in practice), causing the junction parasitic capacity C of the photodiode [[C]] PD to be discharged.

[0031] Figure 4 schematically illustrates the operation of the light sensor circuit by a flow of electric charge q of the transistor Q1 when detecting a light signal. The junction parasitic capacity C of the photodiode PD is discharged for initializing the light sensor circuit before detecting a light signal and then charged. In this case, the output voltage V_{pd} (a terminal voltage of the photodiode PD) with an elapse of a specified time from the initializing timing becomes a value corresponding to the quantity of incident light L_s . In other words, the light sensor circuit after initialization can obtain a discharging characteristic with a specified time constant in response to a change in the quantity of incident light.